

General Description

These P-Channel enhancement mode power field effect transistors use advanced trench technology and design to provide excellent RDS(ON) . This device is suitable for use as a load switch or in PWM applications.

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	-80	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	-56	A
I_{DM}	Pulsed Drain Current	-320	A
EAS	Single Pulse Avalanche Energy ¹	324	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	135	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	50	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.93	°C/W

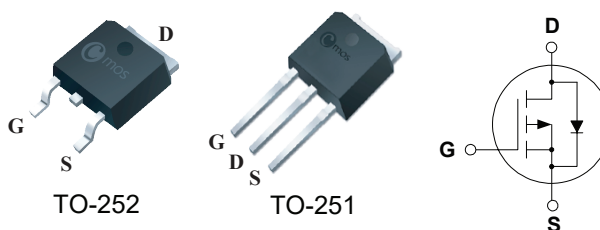
Product Summary

BVDSS	RDS(on) max.	ID
-60V	16mΩ	-80A

Applications

- DC-DC Converters
- Load Switches
- BLDC Motor driver

TO-252 / 251 Pin Configuration



Type	Package	Marking
CMD80P06B	TO-252	CMD80P06B
CMU80P06B	TO-251	CMU80P06B

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V$, $I_D=-28A$	---	13	16	mΩ
		$V_{GS}=-4.5V$, $I_D=-20A$	---	21	28	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.0	---	-3.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-60V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-10V$, $I_D=-20A$	---	24	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	40	---	Ω
Q_g	Total Gate Charge	$V_{DD}=-30V$, $I_D=-50A$ $V_{GS}=-10V$	---	110	---	nC
Q_{gs}	Gate-Source Charge		---	20	---	
Q_{gd}	Gate-Drain Charge		---	28	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-30V$, $V_{GS}=-10V$, $R_L=0.6\Omega$ $R_G=6\Omega$, $I_D=-50A$	---	15	---	ns
T_r	Rise Time		---	70	---	
$T_{d(off)}$	Turn-Off Delay Time		---	175	---	
T_f	Fall Time		---	175	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	5700	---	pF
C_{oss}	Output Capacitance		---	280	---	
C_{rss}	Reverse Transfer Capacitance		---	260	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-80	A
I_{SM}	Pulsed Source Current		---	---	-320	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=-28A$	---	-0.89	-1.5	V

Note :

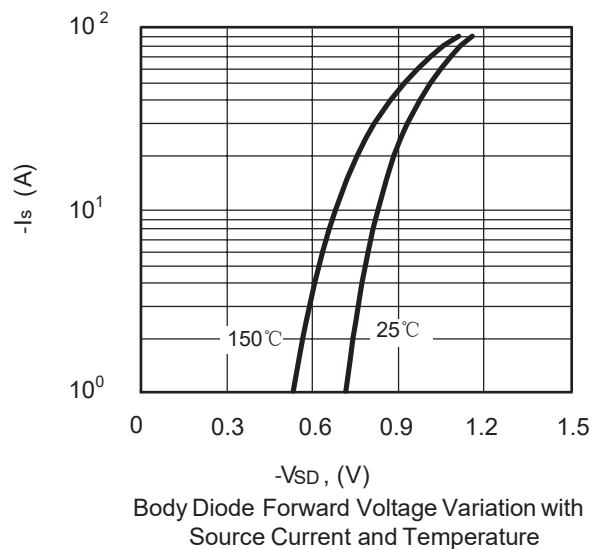
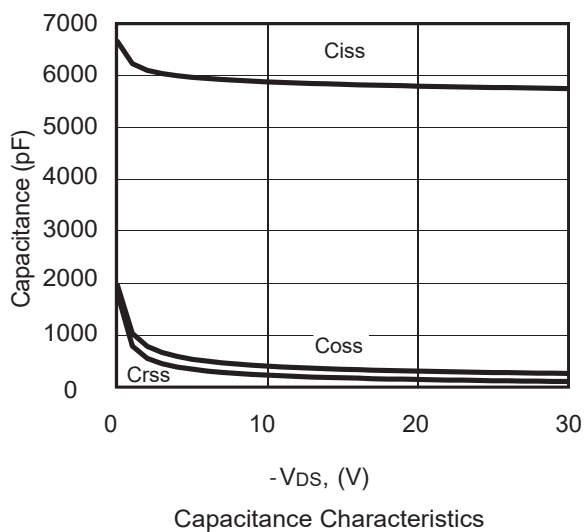
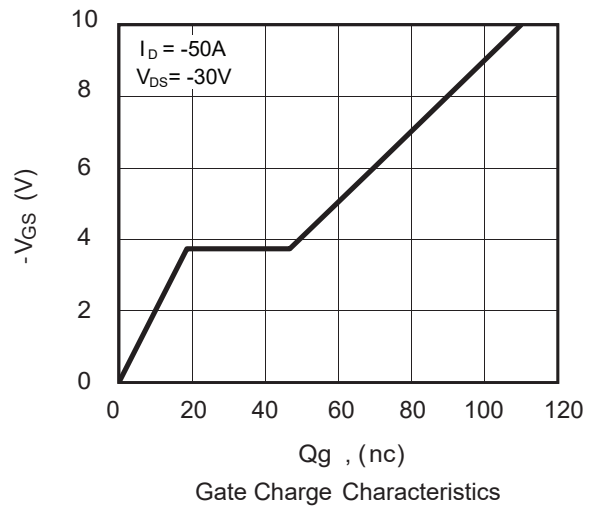
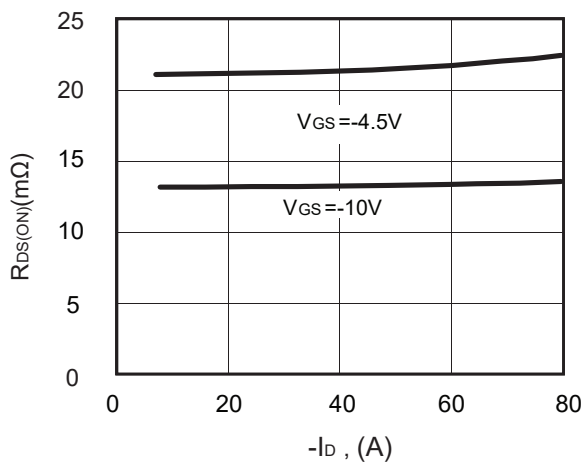
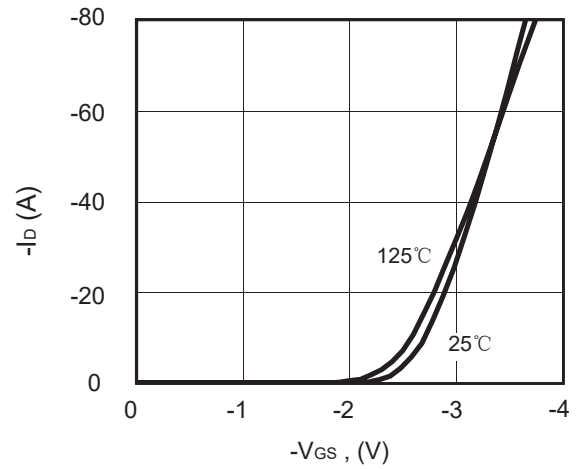
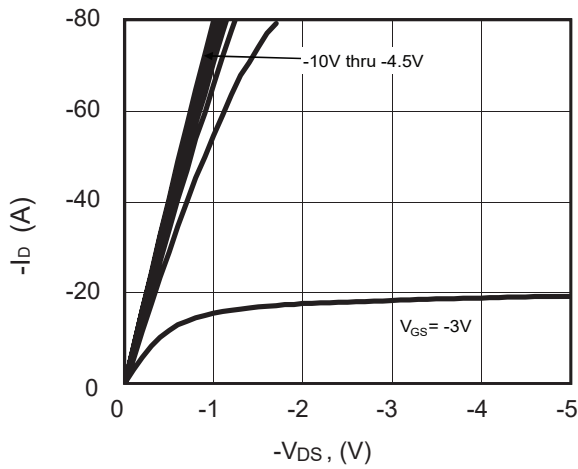
1.The EAS data shows Max. rating . The test condition is $V_{DD}=-30V$, $V_{GS}=-10V$, $L=0.5\text{mH}$, $I_{AS}=-36A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

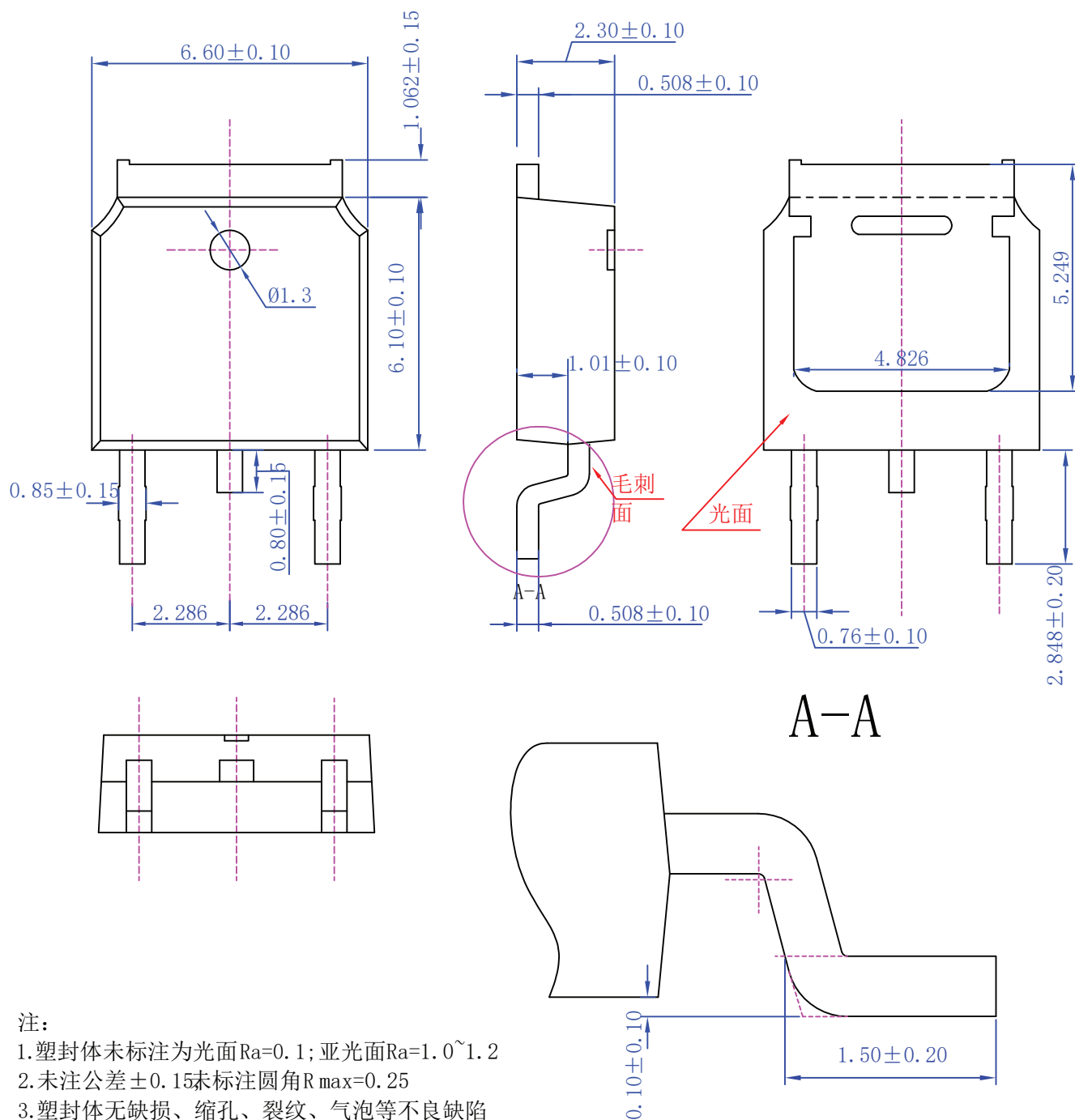
Typical Characteristics



Package Dimension

TO-252

Unit :mm



Package Dimension

TO-251A Unit :mm

